

In re the Application of Rule 53(b) Divisional: MORIIZUMI, Kiyokazu et al.

U.S Serial No. 09/705,897 (Parent)

Preliminary Amendment

**Amendments to the Specification:**

Please amend the specification by inserting after the title:

This application is a DIVISION of prior application Serial No. 09/705,897 filed  
Patent No. 6,717,262

November 6, 2000

Please amend the paragraph beginning at page 6, line 9, as follows:

On the other hand, on the thin-film multilayer interconnect substrate D part 32 is mounted an LSI chip 34 "flipped" top-side down, by means of solder bumps 33 35 made of Pb-Sn or the like, and cooling fins 36 are mounted on the reverse side of the LSI chip 34 to dissipate the heat generated in the LSI.

Please amend the paragraph beginning at page 16, line 29, as follows:

Next, as shown in Fig. 7G, a W tungsten (W) film 18 with a maximum thickness of several thousand angstroms, for example, 3000 Å, is deposited by sputtering over the entire surface.

Please amend the paragraph beginning at page 21, line 32, as follows:

In each of the above embodiments, W tungsten (W) is used to form the film that acts as a stopper in the CMP process, but the material is not limited to W; the only requirement here is that the film be a metal film harder than the Ni electroplated pad to be polished, and even an insulating film may be used.